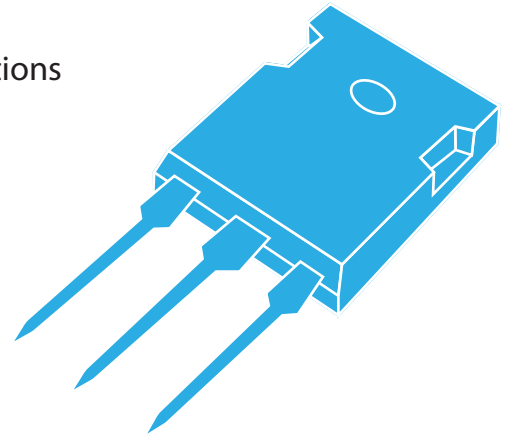


P CHANNEL LATERAL MOSFET

P Channel Lateral Mosfet

- Designed specifically for linear audio amplifier applications
- High-speed for high bandwidth amplifiers
- Reduced $V_{ds\ sat}$
- High voltage rating - 200V
- TO-247 plastic package
- Enhanced oscillation suppression in multi-device applications
- Complementary N-channel available – ECX10N20



ABSOLUTE MAXIMUM RATINGS

($T_C = 25^\circ\text{C}$ unless otherwise stated)

V_{DSS}	Drain – Source Voltage	-200V
V_{GSS}	Gate – Source Voltage	+/-14V
I_D	Continuous Drain Current	-8A
I_{DR}	Body Drain Diode Current	-8A
P_D	Allowable Power Dissipation* $T_{case} = 25^\circ\text{C}$	125W
T_{ch}	Channel Temperature	150°C
T_{stg}	Storage Temperature Range	-55 to +150°C

*Thermal Resistance, Junction To Case 1.0°C/W

ELECTRICAL CHARACTERISTICS (TC = 25°C unless otherwise stated)

Symbols	Parameters	Test Conditions		Min.	Typ	Max.	Units
BV_{DSX}	Drain-Source Breakdown Voltage	$V_{GS} = 10V$	$I_D = -10mA$	-200			V
$V_{GS(off)}$	Gate-Source Cut-off Voltage	$V_{DS} = 10V$	$I_D = -100mA$	-0.15		-1.5	V
$V_{DS(sat)}^*$	Drain-Source Saturation Voltage	$V_{GD} = 0$	$I_D = -8A$			-10	V
$ y_{fs} ^*$	Forward Transfer Admittance	$V_{DS} = 10V$	$I_{DS} = *3A$	0.7		2	S(Ω)
I_{DSX}	Drain-Source Cut-Off Current	$V_{GS} = 10V$	$V_{DS} = *200V$			-10	mA

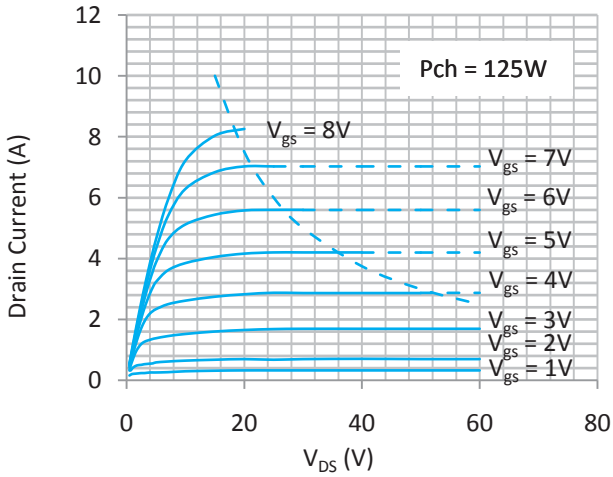
* Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2%

DYNAMIC CHARACTERISTICS

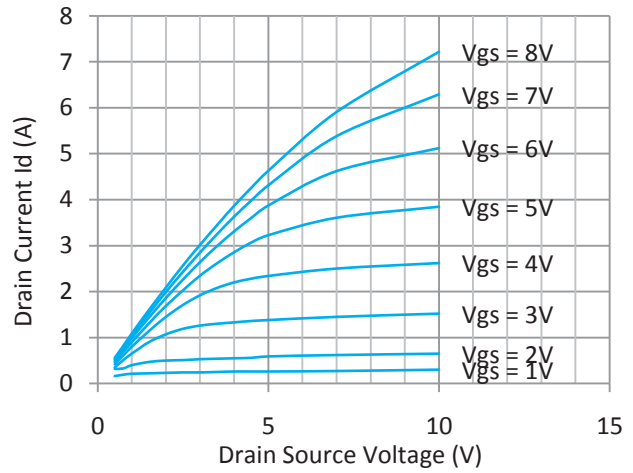
Symbols	Parameters	Test Conditions	Min.	Typ	Max.	Units
C_{iss}	Input Capacitance			500		pF
C_{oss}	Output Capacitance	$V_{GS} = 0$ $V_{DS} = 10V$		300		pF
C_{rss}	Reverse Transfer Capacitance	$f = 1.0MHz$		10		pF
t_{on}	Turn-On Time	$V_{DS} = -20V$		100		ns
t_{off}	Turn-Off Time	$I_D = -7A$		50		ns

GENERAL CHARACTERISTICS (T = 25°C unless otherwise stated)

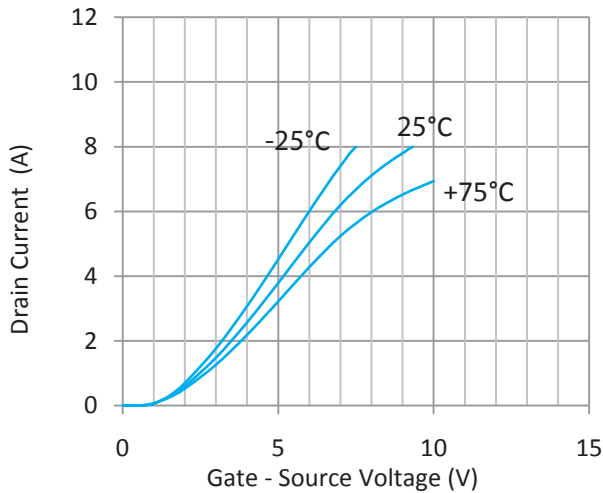
Typical Output Characteristics



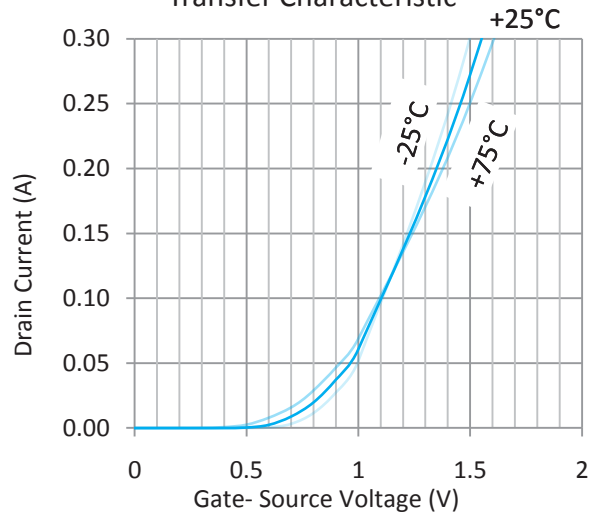
Typical Output Characteristics



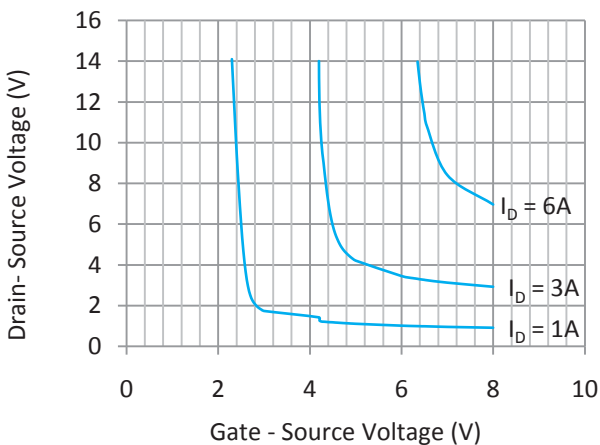
Transfer Characteristic



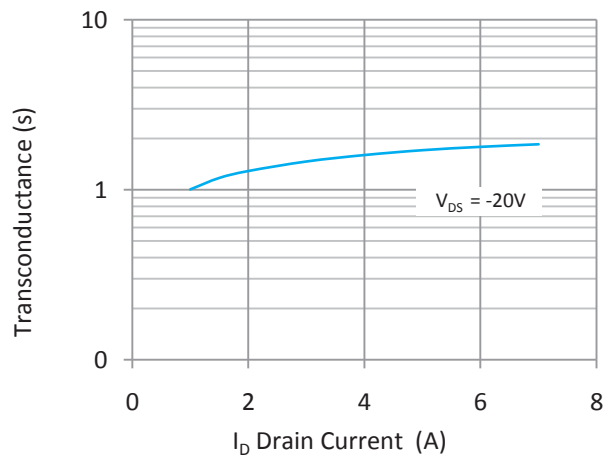
Transfer Characteristic



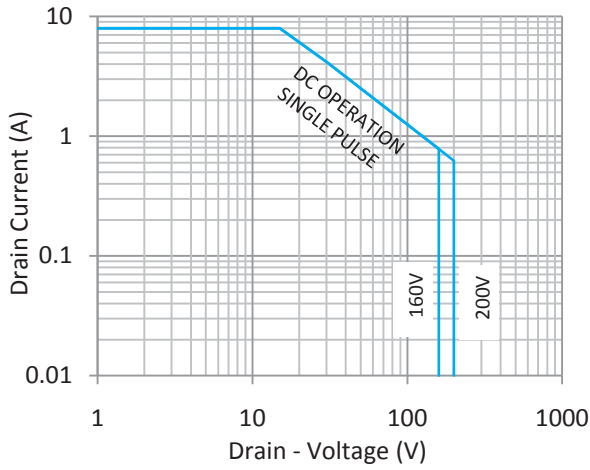
Drain - Source Voltage vs Gate - Source Voltage



Transconductance



Safe Operating Area



Typical Capacitance vs Gate -Source Voltage

$V_{DS} = 10$
 $f = 1 \text{ MHz}$

